

Gallium Arsenide Schottky Rectifier

$$\begin{aligned} I_{DC} &= 12 \text{ A} \\ V_{RRM} &= 250 \text{ V} \\ C_{Junction} &= 18 \text{ pF} \end{aligned}$$

V_{RSM} V	V_{RRM} V	Type	Marking on product
250	250	DGS 9-025AS	9A25AS
250	250	DGS 10-025A	DGS 10-025A
250	250	DGSK 20-025A	DGSK 20-025A

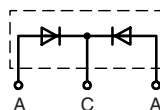
Single



Single



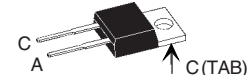
Common cathode



TO-252 AA



TO-220 AC



TO-220 AB



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FAV}	$T_C = 25^\circ\text{C}$; DC	12	A
I_{FAV}	$T_C = 90^\circ\text{C}$; DC	9	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	20	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	34	W
M_d	mounting torque (TO-220)	0.4...0.6	Nm

Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
 - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

Applications

- MHz switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	1.3	1.3 mA mA
V_F	$I_F = 5 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 5 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	1.3 1.2	V V
C_J	$V_R = 100 \text{ V}$; $T_{VJ} = 125^\circ\text{C}$	18	pF
R_{thJC}			4.4 K/W
R_{thCH}	TO-220	0.5	K/W
Weight	TO-252	0.3	g
	TO-220	2	g

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

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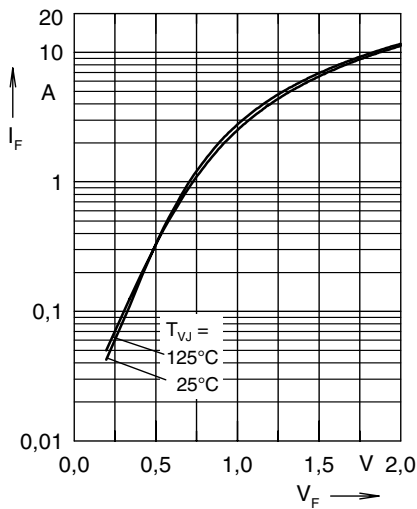


Fig. 1 typ. forward characteristics

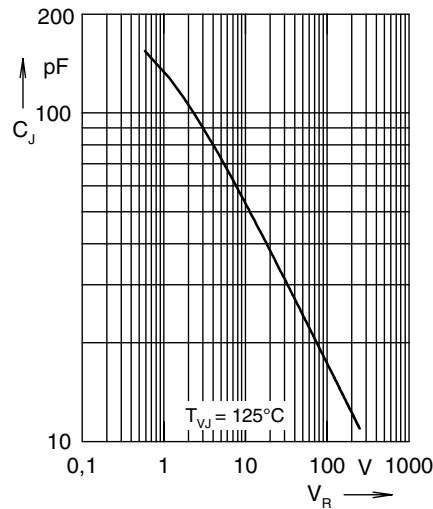


Fig. 2 typ. junction capacity versus blocking voltage

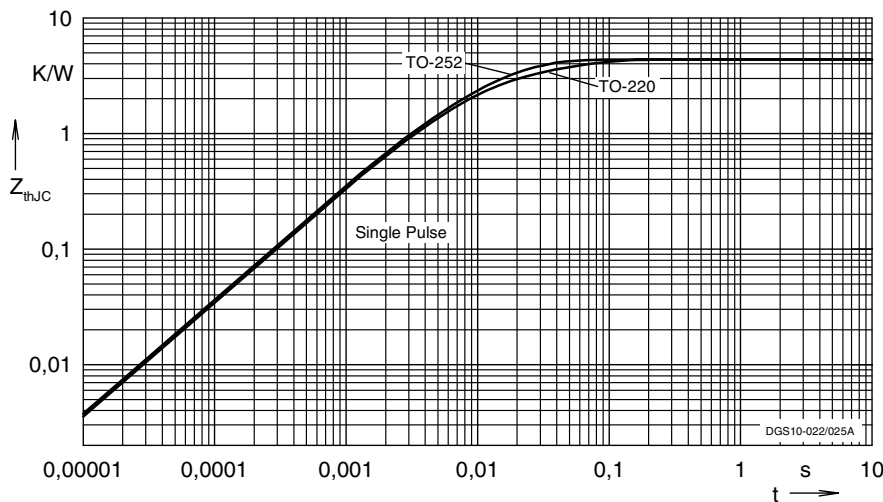
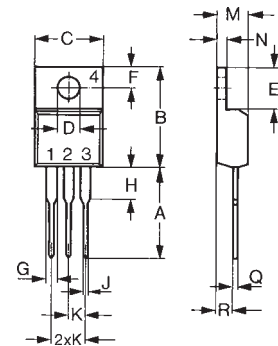


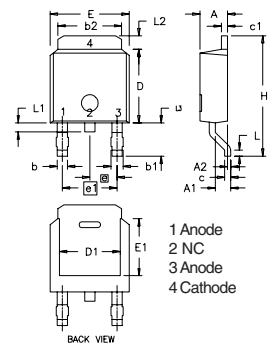
Fig. 3 typ. thermal impedance junction to case

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.38	0.56	0.015	0.022
R	2.29	2.79	0.090	0.110

Outlines TO-252 AA



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

Note:

explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

	Rectifier Diode	GaAs Schottky Diode
conduction	by majority + minority carriers	by majority carriers only
forward characteristics	V_F (I_F)	V_F (I_F), see Fig. 1
turn off characteristics	extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr})	reverse current charges junction capacity C_J , see Fig. 2; not temperature dependant
turn on characteristics	delayed saturation leads to V_{FR}	no turn on overvoltage peak